

IGBT

IGBT with integrated diode in packages offering space saving advantage

IKD06N60RFA

TRENCHSTOP™ RC-Series for hard switching applications up to 30 kHz

Data sheet

IGBT with integrated diode in packages offering space saving advantage

Features:

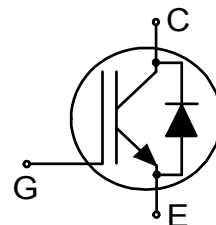
TRENCHSTOP™ Reverse Conducting (RC) technology for 600V applications offering

- Optimized Eon, Eoff and Qrr for low switching losses
- Operating range of 4 to 30kHz
- Smooth switching performance leading to low EMI levels
- Very tight parameter distribution
- Maximum junction temperature 175°C
- Short circuit capability of 5μs
- Best in class current versus package size performance
- Qualified according to AECQ101
- Pb-free lead plating; RoHS compliant (solder temperature 260°C, MSL1)

Complete product spectrum and PSpice Models:
<http://www.infineon.com/igbt/>

Applications:

- Piezo injection
- HID lighting
- Low power motor drives



Key Performance and Package Parameters

Type	V _{CE}	I _C	V _{CEsat} , T _{vj} =25°C	T _{vjmax}	Marking	Package
IKD06N60RFA	600V	6A	2.2V	175°C	K06DRFA	PG-TO252-3

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Maximum Ratings

For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_{vj} \geq 25^{\circ}\text{C}$	V_{CE}	600	V
DC collector current, limited by T_{vjmax} $T_C = 25^{\circ}\text{C}$ $T_C = 100^{\circ}\text{C}$	I_C	12.0 6.0	A
Pulsed collector current, t_p limited by $T_{vjmax}^{1)}$	I_{Cpuls}	18.0	A
Turn off safe operating area $V_{CE} \leq 600\text{V}$, $T_{vj} \leq 175^{\circ}\text{C}$, $t_p = 1\mu\text{s}^{1)}$	-	18.0	A
Diode forward current, limited by T_{vjmax} $T_C = 25^{\circ}\text{C}$ $T_C = 100^{\circ}\text{C}$	I_F	12.0 6.0	A
Diode pulsed current, t_p limited by $T_{vjmax}^{1)}$	I_{Fpuls}	18.0	A
Gate-emitter voltage	V_{GE}	± 20	V
Short circuit withstand time $V_{GE} = 15.0\text{V}$, $V_{CC} \leq 400\text{V}$ Allowed number of short circuits < 1000 Time between short circuits: $\geq 1.0\text{s}$ $T_{vj} = 150^{\circ}\text{C}$	t_{SC}	5	μs
Power dissipation $T_C = 25^{\circ}\text{C}$	P_{tot}	100.0	W
Operating junction temperature	T_{vj}	$-40\dots+175$	$^{\circ}\text{C}$
Storage temperature	T_{stg}	$-55\dots+150$	$^{\circ}\text{C}$
Soldering temperature, reflow soldering (MSL1 according to JEDEC J-STA-020)		260	$^{\circ}\text{C}$

Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
Characteristic				
IGBT thermal resistance, ²⁾ junction - case	$R_{th(j-c)}$		1.50	K/W
Diode thermal resistance, ³⁾ junction - case	$R_{th(j-c)}$		3.60	K/W
Thermal resistance, min. footprint junction - ambient	$R_{th(j-a)}$		75	K/W
Thermal resistance, 6cm ² Cu on PCB junction - ambient	$R_{th(j-a)}$		50	K/W

¹⁾ Defined by design. Not subject to production test.

²⁾ R_{th}/Z_{th} based on single cooling pulse. Please be aware that a correct R_{th} measurement of the IGBT, is not possible using a thermocouple.

³⁾ R_{th}/Z_{th} based on single cooling pulse. Please be aware that a correct R_{th} measurement of the Diode, is not possible using a thermocouple.

Electrical Characteristic, at $T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE} = 0V, I_C = 0.20mA$	600	-	-	V
Collector-emitter saturation voltage	V_{CESat}	$V_{GE} = 15.0V, I_C = 6.0A$ $T_{vj} = 25^{\circ}C$ $T_{vj} = 175^{\circ}C$	- -	2.20 2.30	2.50 -	V
Diode forward voltage	V_F	$V_{GE} = 0V, I_F = 6.0A$ $T_{vj} = 25^{\circ}C$ $T_{vj} = 175^{\circ}C$	- -	2.10 2.00	2.40 -	V
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C = 0.11mA, V_{CE} = V_{GE}$	4.3	5.0	5.7	V
Zero gate voltage collector current	I_{CES}	$V_{CE} = 600V, V_{GE} = 0V$ $T_{vj} = 25^{\circ}C$ $T_{vj} = 175^{\circ}C$	- -	- 250.0	40.0 -	μA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0V, V_{GE} = 20V$	-	-	100	nA
Transconductance	g_{fs}	$V_{CE} = 20V, I_C = 6.0A$	-	2.9	-	S
Integrated gate resistor	r_G			none		Ω

Electrical Characteristic, at $T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Dynamic Characteristic						
Input capacitance	C_{ies}	$V_{CE} = 25V, V_{GE} = 0V, f = 1MHz$	-	470	-	pF
Output capacitance	C_{oes}		-	24	-	
Reverse transfer capacitance	C_{res}		-	14	-	
Gate charge	Q_G	$V_{CC} = 480V, I_C = 6.0A,$ $V_{GE} = 15V$	-	48.0	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L_E		-	7.0	-	nH
Short circuit collector current Max. 1000 short circuits Time between short circuits: $\geq 1.0s$	$I_{C(SC)}$	$V_{GE} = 15.0V, V_{CC} \leq 400V,$ $t_{SC} \leq 5\mu s$ $T_{vj} = 25^{\circ}C$	-	48	-	A

Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic, at $T_{vj} = 25^{\circ}\text{C}$						
Turn-on delay time	$t_{d(\text{on})}$	$T_{vj} = 25^{\circ}\text{C},$ $V_{CC} = 400\text{V}, I_C = 6.0\text{A},$ $V_{GE} = 0.0/15.0\text{V},$ $r_G = 23.0\Omega, L\sigma = 50\text{nH},$ $C\sigma = 30\text{pF}$ $L\sigma, C\sigma$ from Fig. E	-	8	-	ns
Rise time	t_r		-	8	-	ns
Turn-off delay time	$t_{d(\text{off})}$		-	105	-	ns
Fall time	t_f		-	22	-	ns
Turn-on energy	E_{on}		-	0.09	-	mJ
Turn-off energy	E_{off}		-	0.09	-	mJ
Total switching energy	E_{ts}		-	0.18	-	mJ

Diode Characteristic, at $T_{vj} = 25^{\circ}\text{C}$

Diode reverse recovery time	t_{rr}	$T_{vj} = 25^{\circ}\text{C},$ $V_R = 400\text{V},$ $I_F = 6.0\text{A},$ $di_F/dt = 770\text{A}/\mu\text{s}$	-	48	-	ns
Diode reverse recovery charge	Q_{rr}		-	0.16	-	μC
Diode peak reverse recovery current	I_{rrm}		-	7.4	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	-195	-	A/ μs

Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic, at $T_{vj} = 175^{\circ}\text{C}$						
Turn-on delay time	$t_{d(on)}$	$T_{vj} = 175^{\circ}\text{C},$ $V_{CC} = 400\text{V}, I_C = 6.0\text{A},$ $V_{GE} = 0.0/15.0\text{V},$ $r_G = 23.0\Omega, L\sigma = 50\text{nH},$ $C\sigma = 30\text{pF}$ $L\sigma, C\sigma$ from Fig. E	-	9	-	ns
Rise time	t_r		-	8	-	ns
Turn-off delay time	$t_{d(off)}$		-	114	-	ns
Fall time	t_f		-	35	-	ns
Turn-on energy	E_{on}		-	0.15	-	mJ
Turn-off energy	E_{off}		-	0.13	-	mJ
Total switching energy	E_{ts}		-	0.28	-	mJ

Diode Characteristic, at $T_{vj} = 175^{\circ}\text{C}$

Diode reverse recovery time	t_{rr}	$T_{vj} = 175^{\circ}\text{C},$ $V_R = 400\text{V},$ $I_F = 6.0\text{A},$ $di_F/dt = 770\text{A}/\mu\text{s}$	-	74	-	ns
Diode reverse recovery charge	Q_{rr}		-	0.34	-	μC
Diode peak reverse recovery current	I_{rrm}		-	10.3	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	-177	-	A/ μs

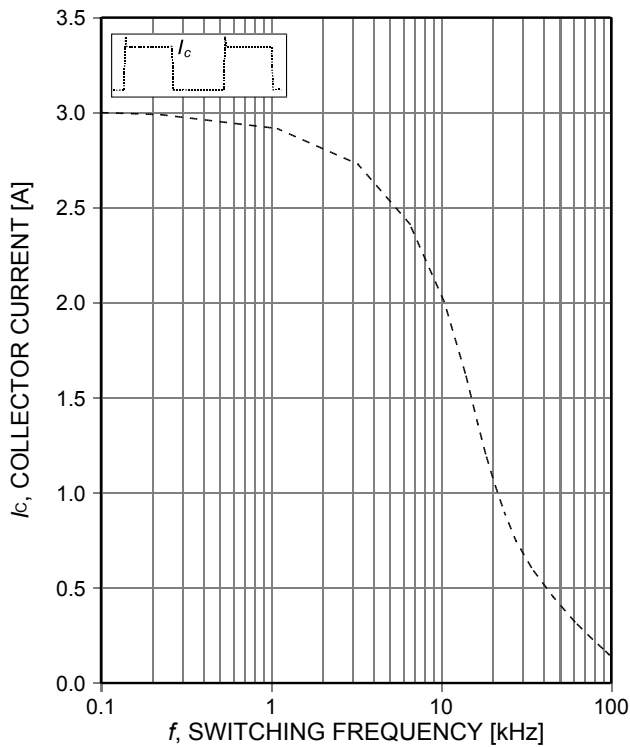


Figure 1. **Collector current as a function of switching frequency**
($T_{vj} \leq 175^\circ\text{C}$, $T_a = 55^\circ\text{C}$, $D = 0.5$, $V_{CE} = 400\text{V}$, $V_{GE} = 15/0\text{V}$, $r_G = 23\Omega$, PCB mounting, $6\text{cm}^2\text{Cu}$, $P_{tot} = 2.4\text{W}$)

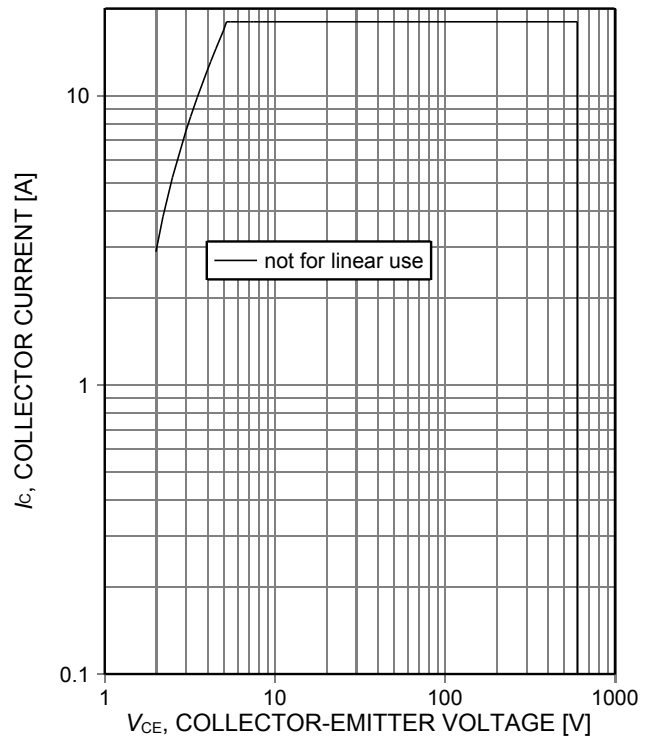


Figure 2. **Forward bias safe operating area**
($D = 0$, $T_C = 25^\circ\text{C}$, $T_{vj} \leq 175^\circ\text{C}$, $V_{GE} = 15\text{V}$, $t_p = 1\mu\text{s}$)

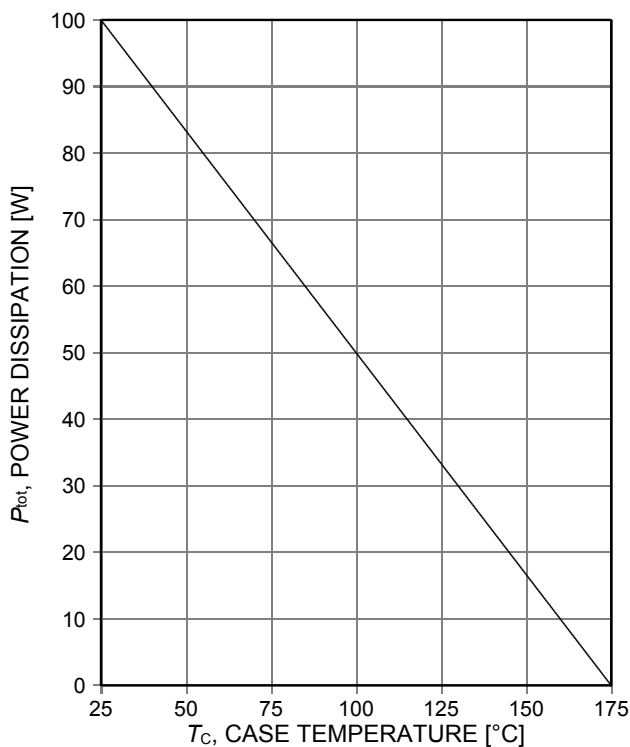


Figure 3. **Power dissipation as a function of case temperature**
($T_{vj} \leq 175^\circ\text{C}$)

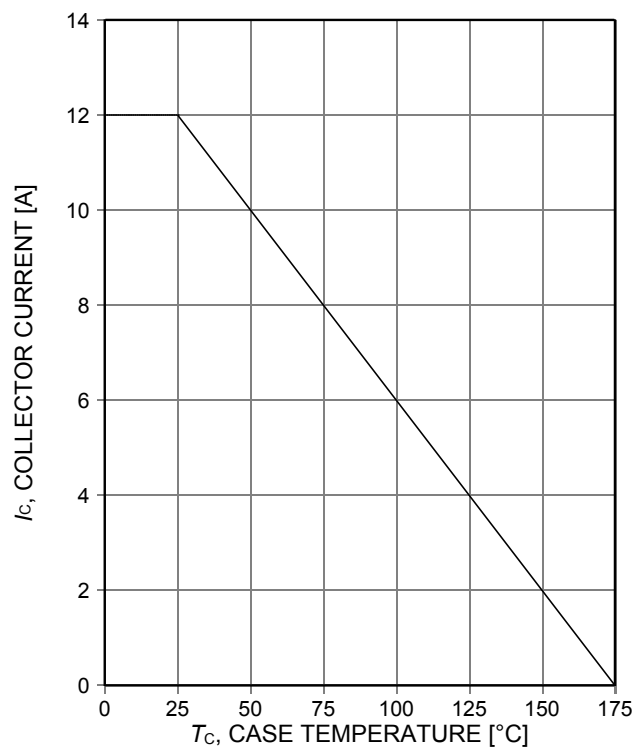


Figure 4. **Collector current as a function of case temperature**
($V_{GE} \geq 15\text{V}$, $T_{vj} \leq 175^\circ\text{C}$)

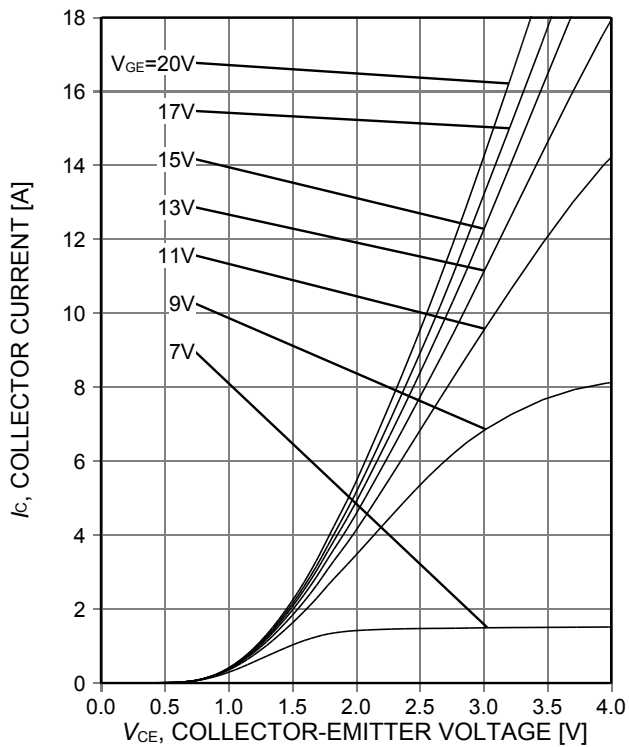


Figure 5. **Typical output characteristic**
($T_{vj}=25^{\circ}\text{C}$)

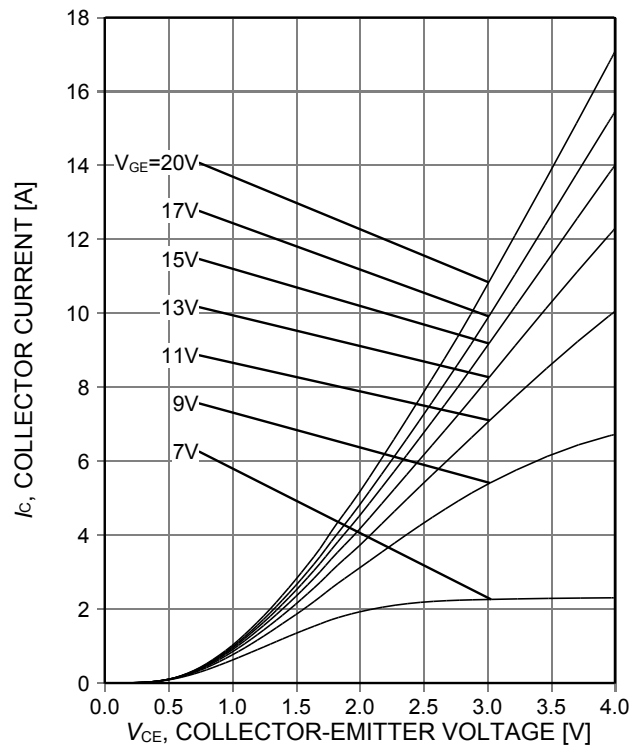


Figure 6. **Typical output characteristic**
($T_{vj}=175^{\circ}\text{C}$)

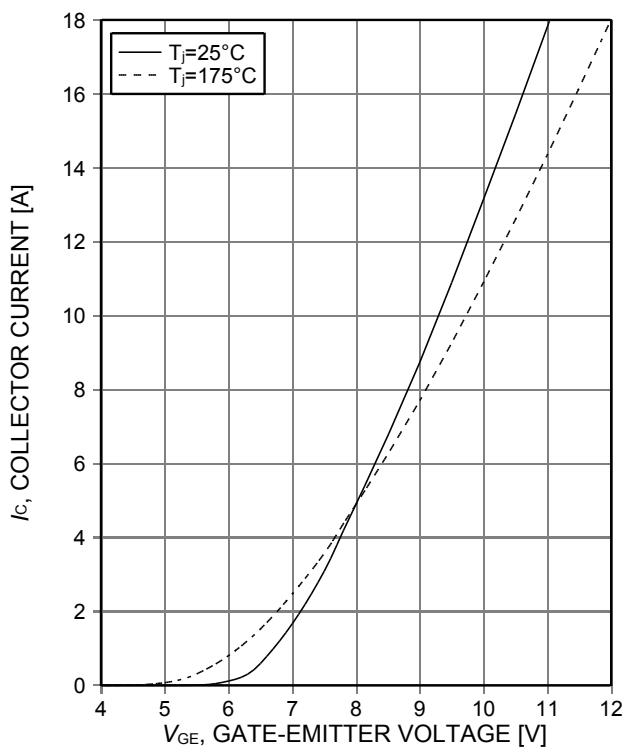


Figure 7. **Typical transfer characteristic**
($V_{CE}=10\text{V}$)

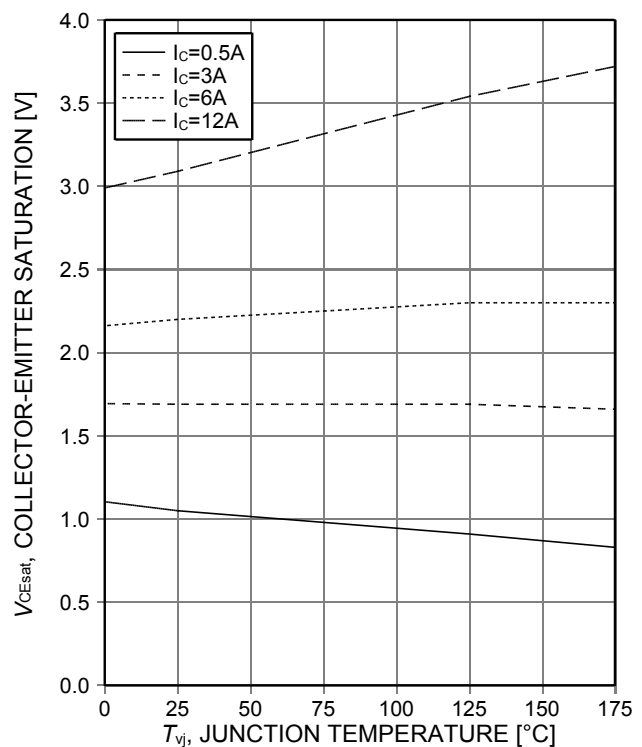


Figure 8. **Typical collector-emitter saturation voltage as a function of junction temperature**
($V_{GE}=15\text{V}$)

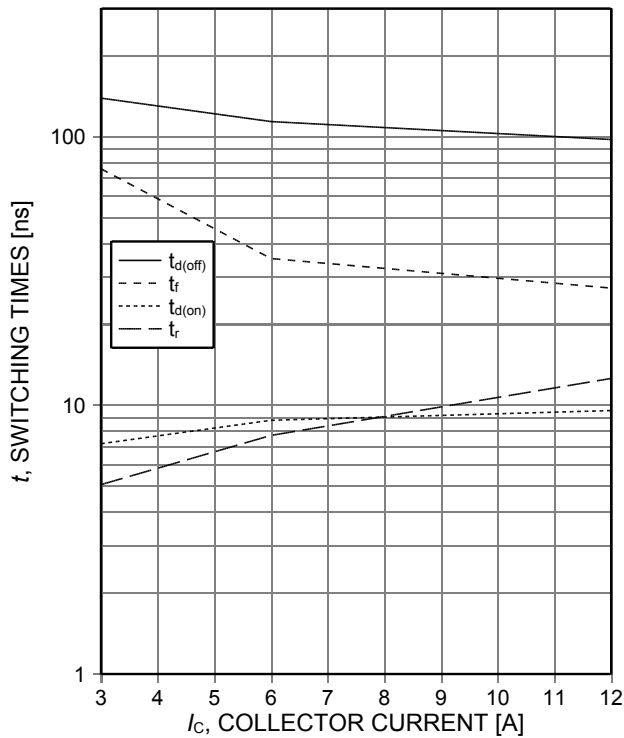


Figure 9. **Typical switching times as a function of collector current**
(inductive load, $T_{vj}=175^{\circ}\text{C}$, $V_{CE}=400\text{V}$, $V_{GE}=15/0\text{V}$, $r_G=23\Omega$, Dynamic test circuit in Figure E)

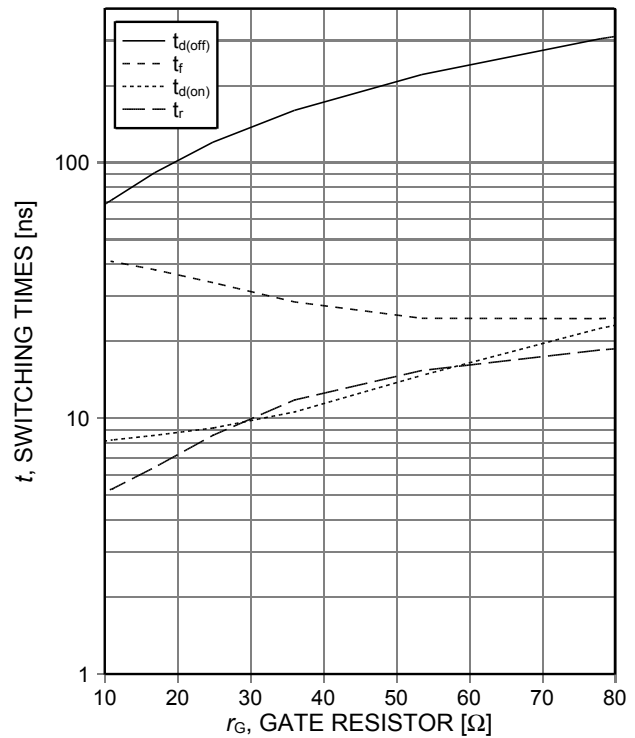


Figure 10. **Typical switching times as a function of gate resistor**
(inductive load, $T_{vj}=175^{\circ}\text{C}$, $V_{CE}=400\text{V}$, $V_{GE}=15/0\text{V}$, $I_C=6\text{A}$, Dynamic test circuit in Figure E)

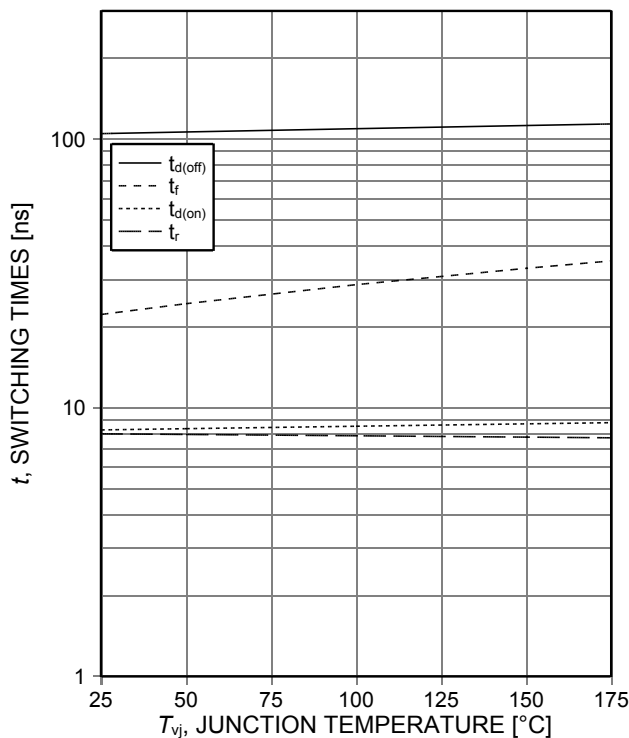


Figure 11. **Typical switching times as a function of junction temperature**
(inductive load, $V_{CE}=400\text{V}$, $V_{GE}=15/0\text{V}$, $I_C=6\text{A}$, $r_G=23\Omega$, Dynamic test circuit in Figure E)

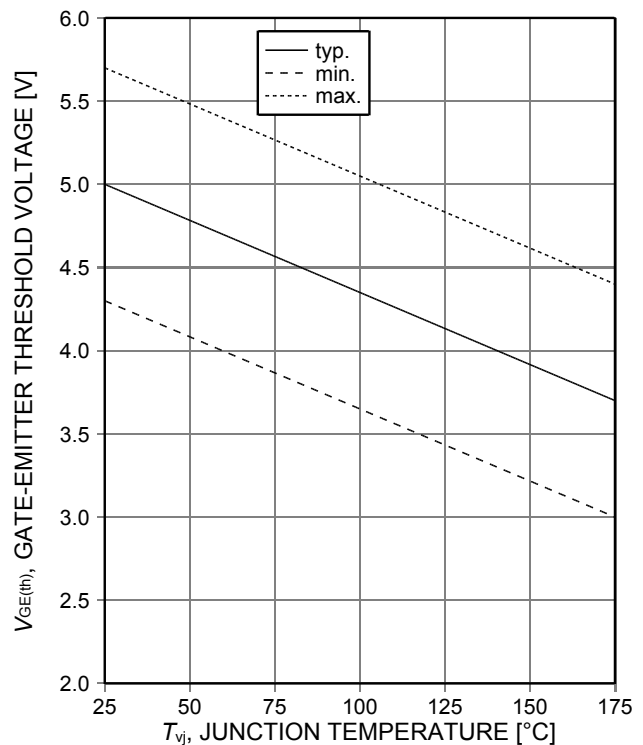


Figure 12. **Gate-emitter threshold voltage as a function of junction temperature**
($I_C=0,11\text{mA}$)

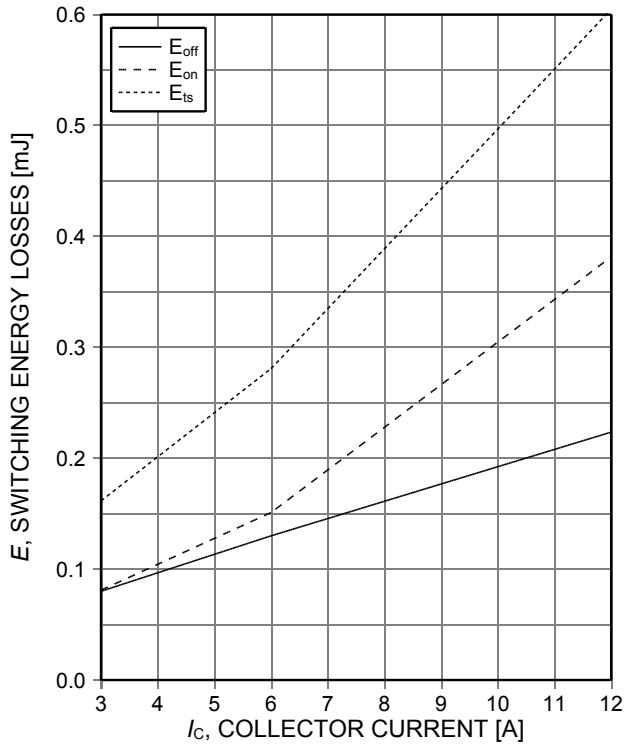


Figure 13. **Typical switching energy losses as a function of collector current**
(inductive load, $T_{vj}=175^{\circ}\text{C}$, $V_{CE}=400\text{V}$, $V_{GE}=15/0\text{V}$, $r_G=23\Omega$, Dynamic test circuit in Figure E)

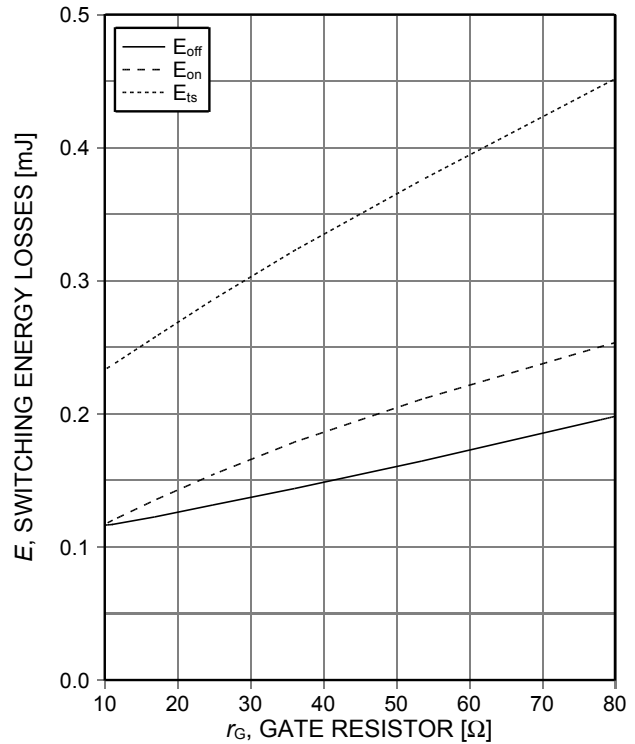


Figure 14. **Typical switching energy losses as a function of gate resistor**
(inductive load, $T_{vj}=175^{\circ}\text{C}$, $V_{CE}=400\text{V}$, $V_{GE}=15/0\text{V}$, $I_C=6\text{A}$, Dynamic test circuit in Figure E)

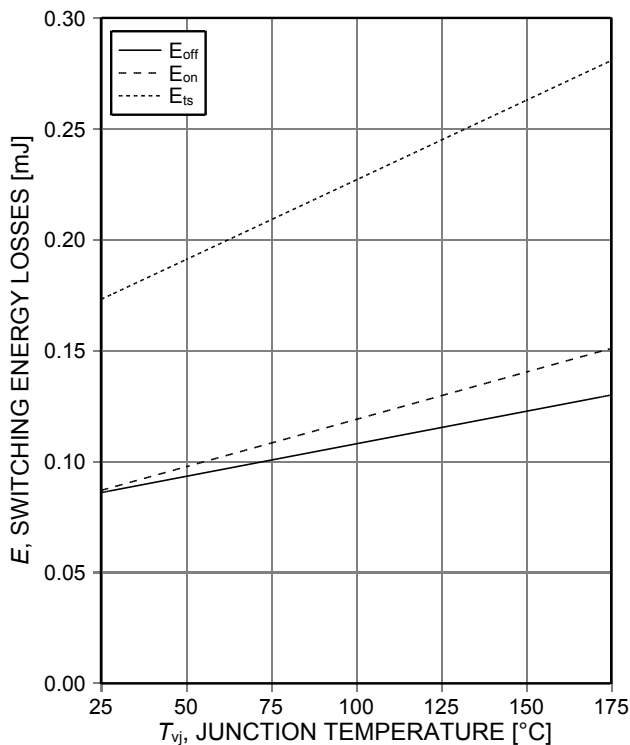


Figure 15. **Typical switching energy losses as a function of junction temperature**
(inductive load, $V_{CE}=400\text{V}$, $V_{GE}=15/0\text{V}$, $I_C=6\text{A}$, $r_G=23\Omega$, Dynamic test circuit in Figure E)

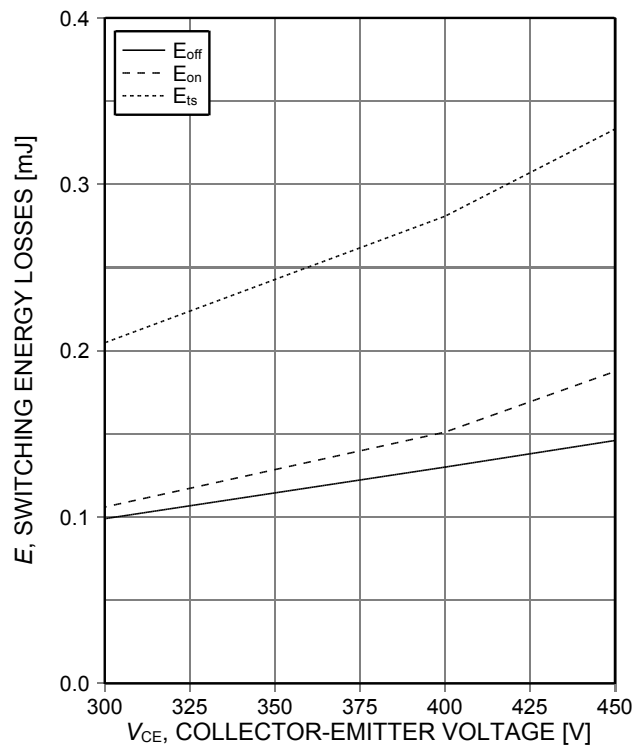


Figure 16. **Typical switching energy losses as a function of collector emitter voltage**
(inductive load, $T_{vj}=175^{\circ}\text{C}$, $V_{GE}=15/0\text{V}$, $I_C=6\text{A}$, $r_G=23\Omega$, Dynamic test circuit in Figure E)

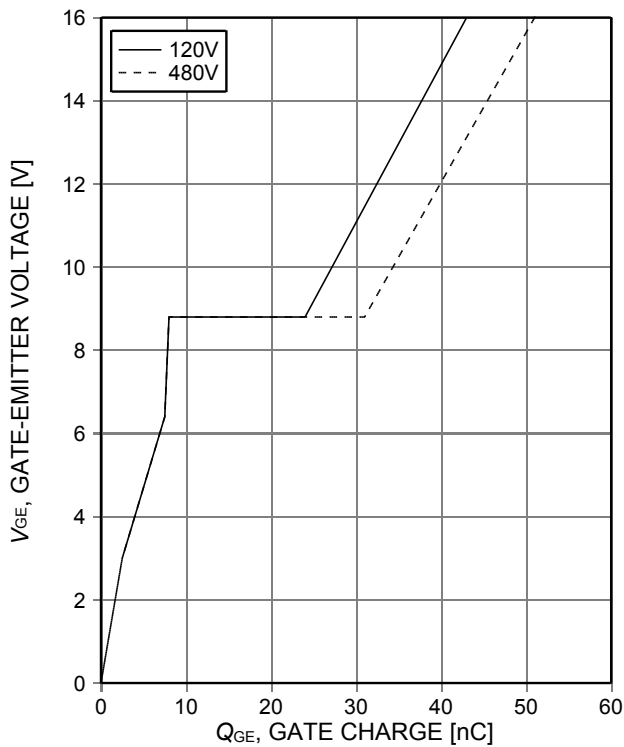


Figure 17. **Typical gate charge**
($I_C=6A$)

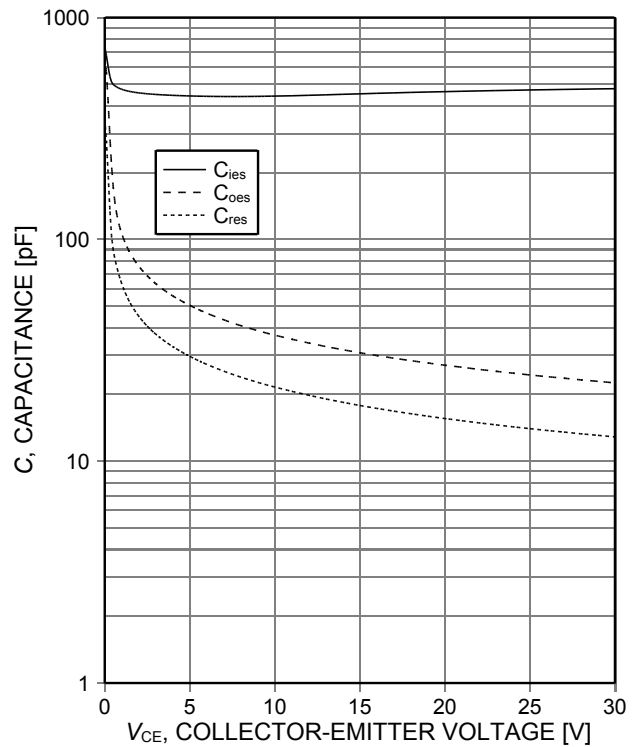


Figure 18. **Typical capacitance as a function of collector-emitter voltage**
($V_{GE}=0V$, $f=1MHz$)

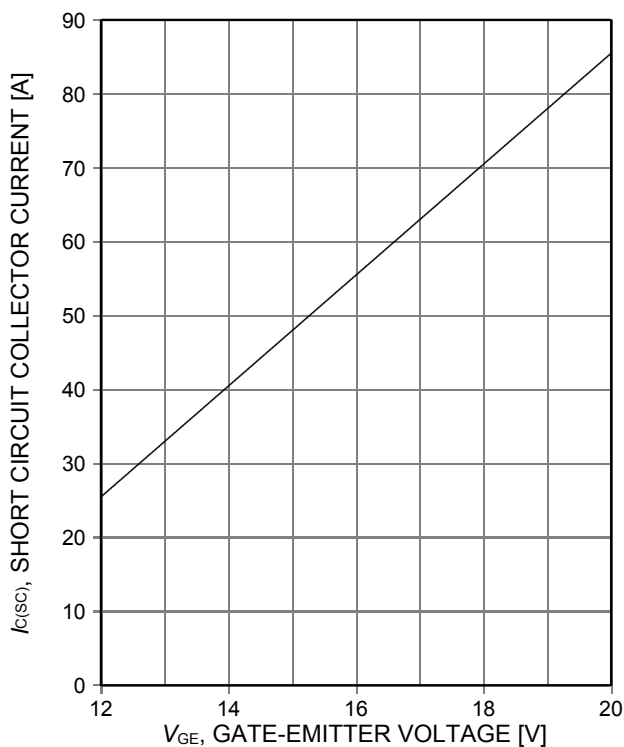


Figure 19. **Typical short circuit collector current as a function of gate-emitter voltage**
($V_{CE} \leq 400V$, start at $T_{vj}=25^\circ C$)

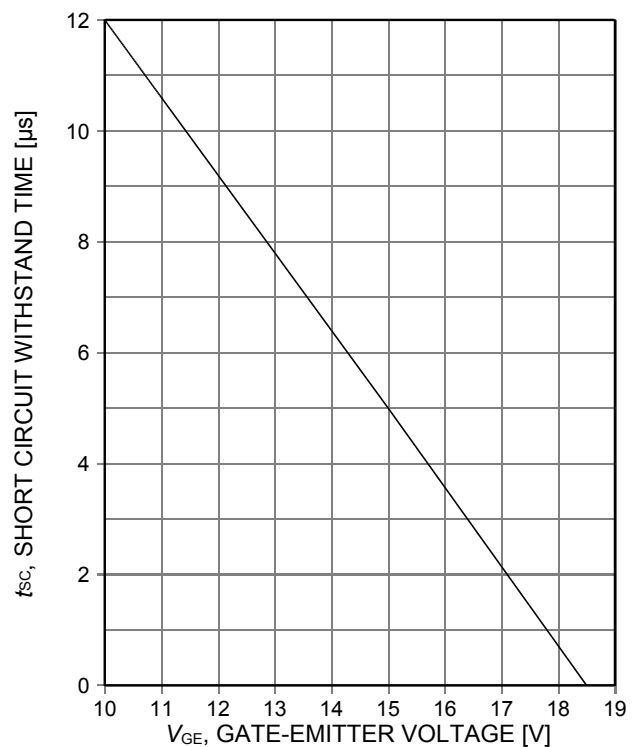


Figure 20. **Short circuit withstand time as a function of gate-emitter voltage**
($V_{CE} \leq 400V$, start at $T_{vj}=150^\circ C$)

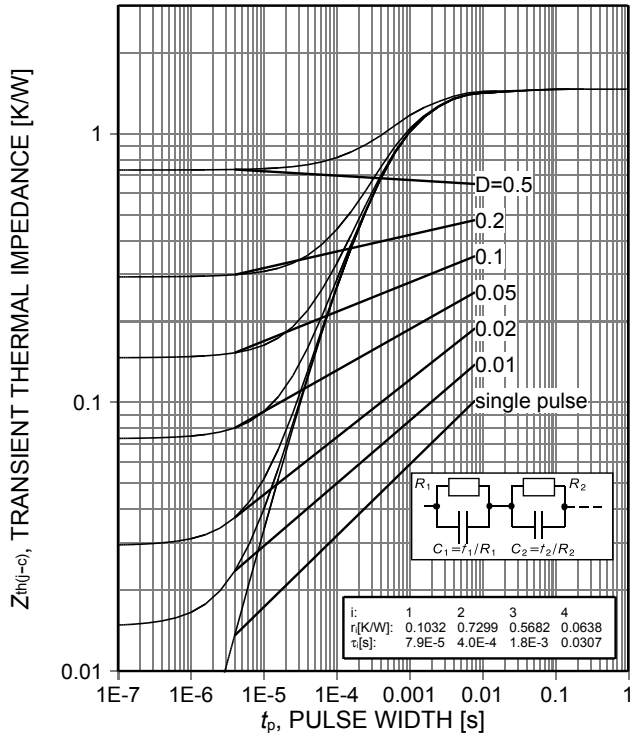


Figure 21. IGBT transient thermal impedance as a function of pulse width ¹⁾ (see page 4)
($D=t_p/T$)

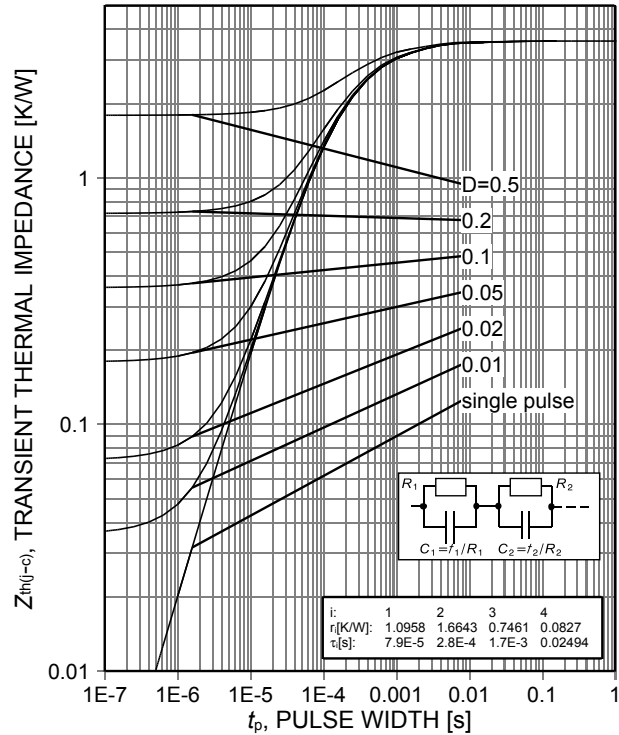


Figure 22. Diode transient thermal impedance as a function of pulse width ²⁾ (see page 4)
($D=t_p/T$)

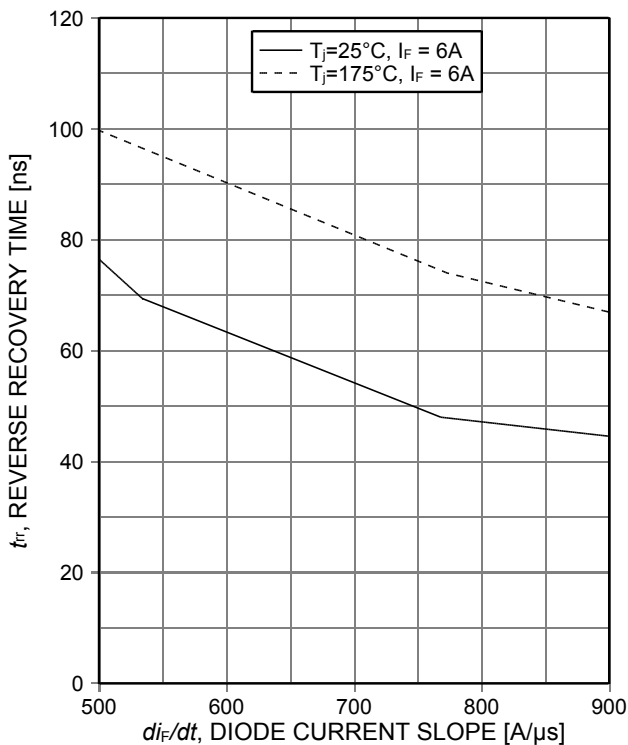


Figure 23. Typical reverse recovery time as a function of diode current slope
($V_R=400V$)

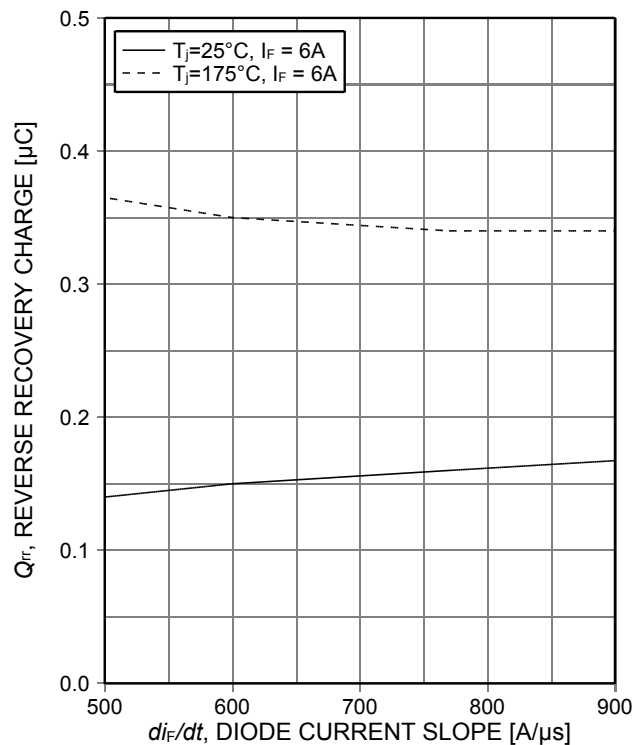


Figure 24. Typical reverse recovery charge as a function of diode current slope
($V_R=400V$)

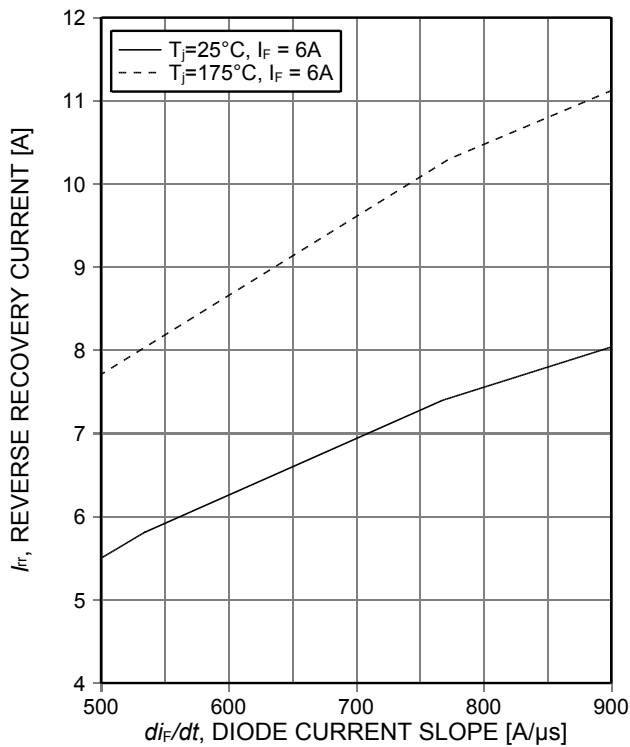


Figure 25. **Typical reverse recovery current as a function of diode current slope**
($V_R=400V$)

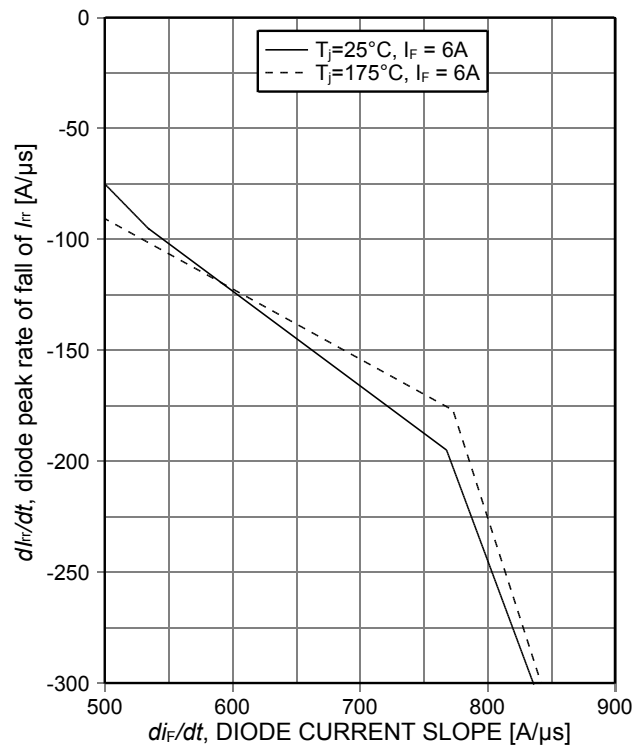


Figure 26. **Typical diode peak rate of fall of reverse recovery current as a function of diode current slope**
($V_R=400V$)

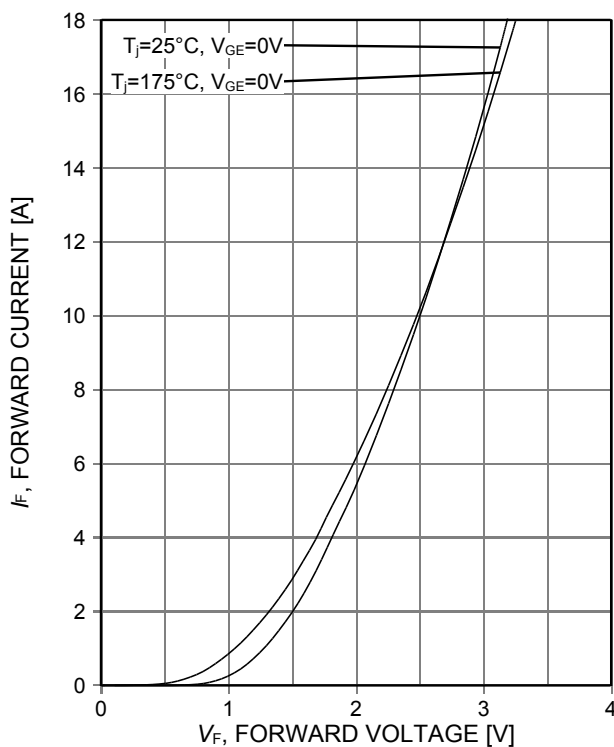


Figure 27. **Typical diode forward current as a function of forward voltage**

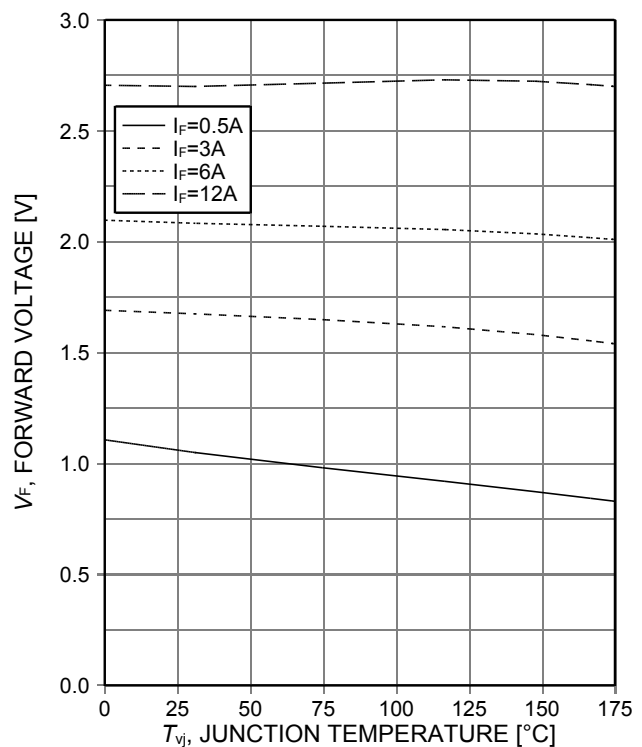
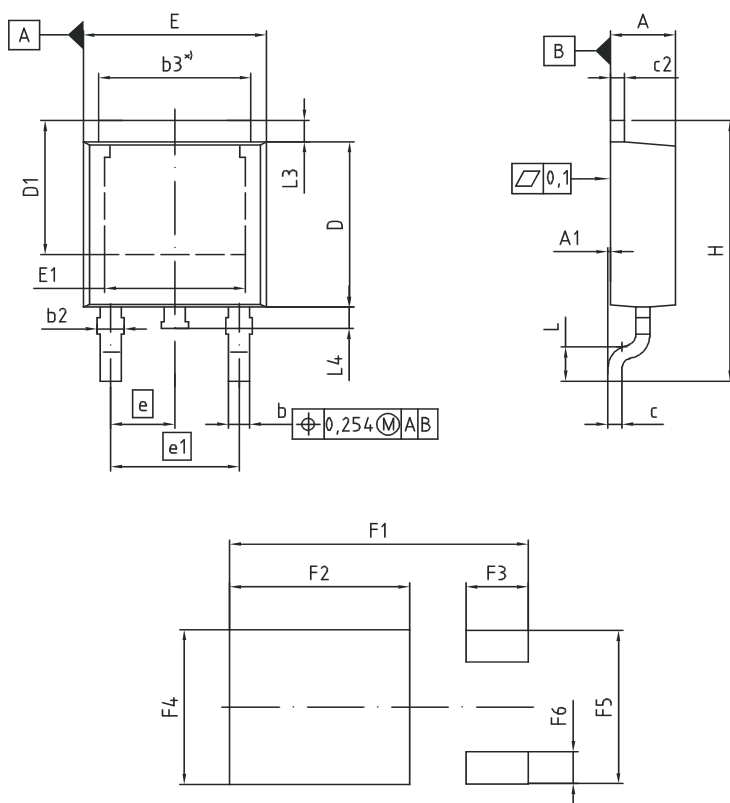


Figure 28. **Typical diode forward voltage as a function of junction temperature**

PG-TO252 -3



*) mold flash not included

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.16	2.41	0.085	0.095
A1	0.00	0.15	0.000	0.006
b	0.64	0.89	0.025	0.035
b2	0.65	1.15	0.026	0.045
b3	5.00	5.50	0.197	0.217
c	0.46	0.60	0.018	0.024
c2	0.46	0.98	0.018	0.039
D	5.97	6.22	0.235	0.245
D1	5.02	5.84	0.198	0.230
E	6.40	6.73	0.252	0.265
E1	4.70	5.21	0.185	0.205
e	2.29 (BSC)		0.090 (BSC)	
e1	4.57		0.180	
N	3		3	
H	9.40	10.48	0.370	0.413
L	1.18	1.70	0.046	0.067
L3	0.90	1.25	0.035	0.049
L4	0.51	1.00	0.020	0.039
F1	10.60		0.417	
F2	6.40		0.252	
F3	2.20		0.087	
F4	5.80		0.228	
F5	5.76		0.227	
F6	1.20		0.047	

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REVISION 04

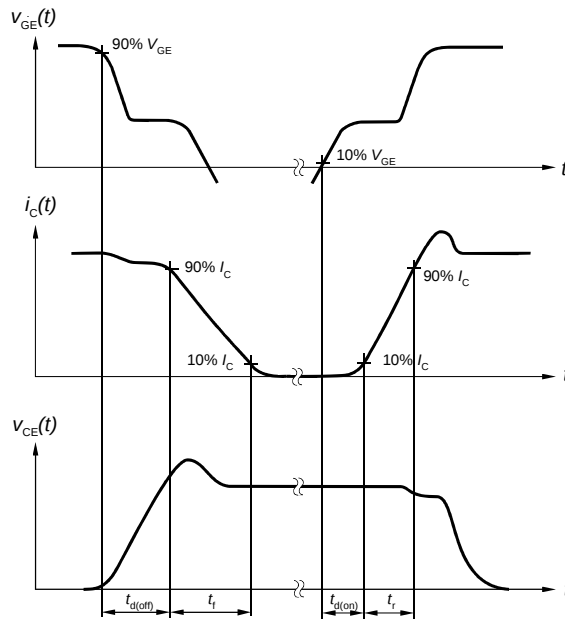


Figure A. Definition of switching times

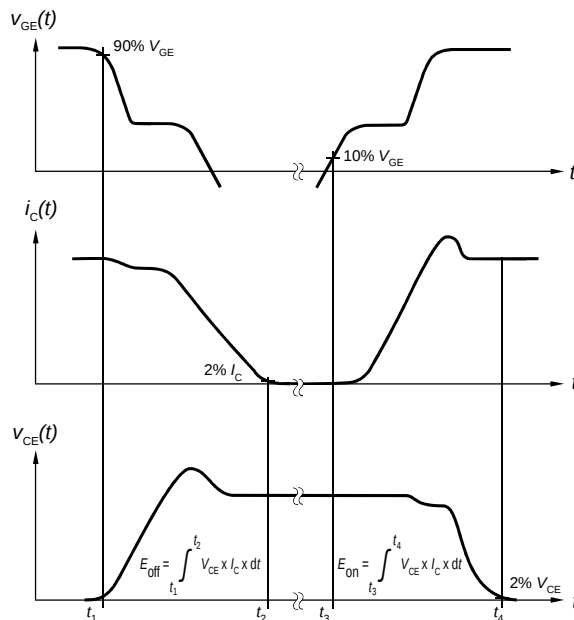


Figure B. Definition of switching losses

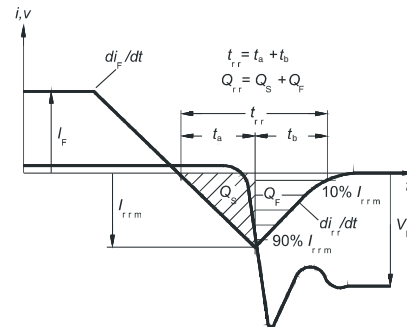


Figure C. Definition of diodes switching characteristics

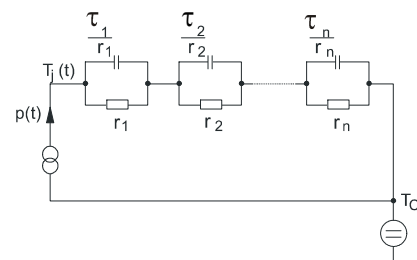
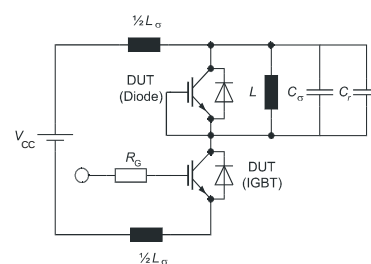


Figure D. Thermal equivalent circuit


Figure E. Dynamic test circuit
Parasitic inductance L_{σ} ,
Parasitic capacitor C_{σ} ,
Relief capacitor C_r
(only for ZVT switching)

Revision History

IKD06N60RFA

Revision: 2014-09-30, Rev. 2.2

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.1	2014-09-23	Final Data sheet
2.2	2014-09-30	Update minor changes

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Information

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office (www.infineon.com).

Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office.

The Infineon Technologies component described in this Data Sheet may be used in life-support devices or systems and/or automotive, aviation and aerospace applications or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support, automotive, aviation and aerospace device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.